12/16/1996

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First Named Inventor	Forbes, Leonard
Group Art Unit	2822
Examiner Nam	Meier, Stephen

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Examiner Initial

USP Document Number

2001/0011744

2002/0020871

2002/0064911

US-3,882,469

US-5,811,865

09/22/1998

US P	ATENT DOCUMENT	S		
Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
08/09/2001	Sung, K.	257	314	03/30/2001
02/21/2002	Forbes, L.	257	315	08/30/2001
05/30/2002	Eitan, B.	438	216	08/28/2001
05/06/1975	Gosney Jr., William M.	340	173R	06/18/1973
09/22/1998	Hodges, Robert L., et	257	411	12/16/1996

257

411

Attorney Docket No: 303.684US3

FOREIGN PATENT DOCUMENTS							
Examiner initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²	

	OTHER	R DOCUMENTS - NON PATENT LITERATURE DOCUMENTS	
Examiner initials*	Cite No 1	include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T
KR		SHI, Y., et al., "Tunneling Leakage Current in Ultrathin (<4 nm) Nitride/Oxide Stack Dielectrics", IEEE Electron Device Letters, 19(10), (Oct. 1998),pp. 388-390	

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